



Packaging (T <sub>j</sub> =25 ; 0 - 100 °C) (FIG.7)	V <sub>p</sub>	1	kV
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ELECTRICAL CHARACTERISTICS(T<sub>j</sub>=25 °C)

Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33Ω	- -	MAX.	50	A
V <sub>GT</sub>		- -	MAX.	1.3	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125 °C R <sub>L</sub> =3.3kΩ	- -	MIN.	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	-	MAX.	80	A
				120	
I <sub>H</sub>	I <sub>T</sub> =1A		MAX.	70	A
dV/dt	V <sub>D</sub> =1070V Gate Open T <sub>j</sub> =125 °C		MIN.	1500	V/μs
(di/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =20V/μs T <sub>j</sub> =125 °C		MIN.	28	A/μs
t <sub>0</sub>	I <sub>G</sub> =80A I <sub>A</sub> =400A I <sub>R</sub> =40A T <sub>j</sub> =25 °C		TYP.	12	μs
t <sub>6</sub>				80	

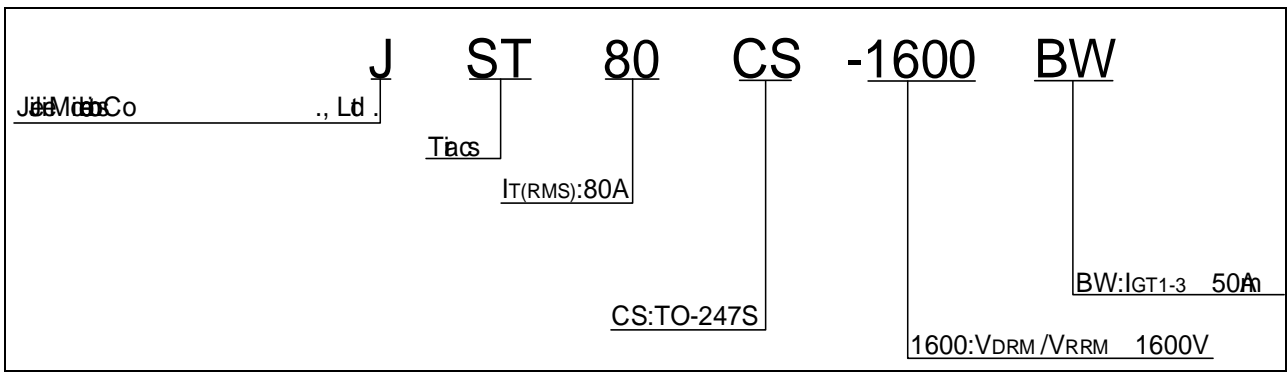
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =120A t <sub>p</sub> =380μs	T <sub>j</sub> =25 °C	1.9	V
V <sub>TO</sub>	T <sub>th</sub>	T <sub>j</sub> =125 °C	0.71	V
R <sub>D</sub>	D <sub>max</sub>	T <sub>j</sub> =125 °C	23	mΩ
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RDM</sub>	T <sub>j</sub> =25 °C	20	μA
I <sub>RDM</sub>		T <sub>j</sub> =125 °C	12	A

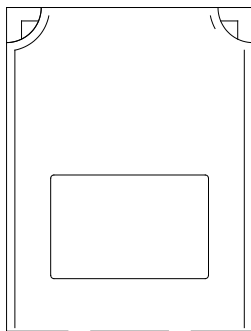
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>			

ORDERING INFORMATION



MARKING



**FIG.1: Main RMS**  
0 100



**FIG.2: RMS 0 - 100**  
0 100

FIG.7



**PACKAGE MECHANICAL DATA**



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